



**30V P-CHANNEL ENHANCEMENT MODE MOSFET** 

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub> max	<b>Ι</b> <sub>D</sub> Τ <sub>A</sub> = +25°C
	50mΩ @ V <sub>GS</sub> = -10V	-3.7A
-30V	60mΩ @ V <sub>GS</sub> = -4.5V	-3.3A
	85mΩ @ V <sub>GS</sub> = -2.5V	-2.7A

# **Description and Applications**

This new generation Small-Signal enhancement mode MOSFET features low on-resistance and fast switching, making it ideal for highefficiency power management applications.

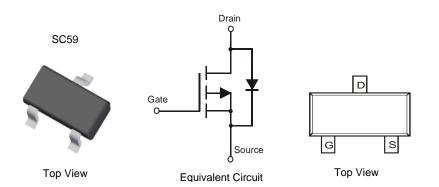
- Motor Control
- Backlighting
- DC-DC Converters
- Power Management Functions

#### Features

- Low Input Capacitance
- Low On-Resistance
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP (Note 4)

#### **Mechanical Data**

- Case: SC-59
- Case Material Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe;
- Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.014 grams (Approximate)



### Ordering Information (Note 5)

Part Number	Case	Packaging
DMG3401LSNQ-7	SC59	3,000/Tape & Reel
DMG3401LSNQ-13	SC59	10,000/Tape & Reel

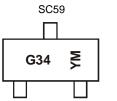
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.</li>

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_grade\_definitions/.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



G34 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: Y = 2011)

M = Month (ex: 9 = September)

#### Date Code Key

Date Code Rey												
Year	2011	2012	2013	2014	2015	2016	2017	2018	2019	2020	2021	2022
Code	Y	Z	А	В	С	D	E	F	G	Н		J
					-				-		-	-
Month	lon	Eab	Mor	Apr	Mov	lun	lul	Aug	Son	Oct	Nov	Dee
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec



## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage	V <sub>DSS</sub>	-30	V	
Gate-Source Voltage		V <sub>GSS</sub>	±12	V
Continuous Drain Current (Note 6) $V_{GS}$ = -10V	ID	-3.0 -2.3	А	
Continuous Drain Current (Note 7) $V_{GS}$ = -10V	ID	-3.7 -2.9	А	
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I <sub>DM</sub>	-30	A	
Maximum Body Diode Continuous Current (Note 7)		ls	-1.5	A

# **Thermal Characteristics**

Characteristic		Symbol	Value	Units	
Total Power Dissipation	(Note 6)	D	0.8	W	
	(Note 7)	PD	1.2		
Thermal Desistance Junction to Ambient	(Note 6)	5	159		
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{ ext{ heta}JA}$	105	°C/W	
Thermal Resistance, Junction to Case	(Note 7)	$R_{\theta JC}$	36		
Operating and Storage Temperature Range	·	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C	

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

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Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)			r	1			
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	-	-	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	IDSS	-	-	-1.0	μA	$V_{DS} = -30V, V_{GS} = 0V$	
Gate-Body Leakage	IGSS	-	-	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.5	-1.0	-1.3	V	$V_{DS} = V_{GS}$ , $I_D = -250 \mu A$	
		-	41	50		$V_{GS} = -10V, I_D = -4A$	
Static Drain-Source On-Resistance	RDS (ON)	-	47	60	mΩ	$V_{GS} = -4.5V, I_D = -3.5A$	
		-	60	85		$V_{GS} = -2.5V, I_D = -2.5A$	
Forward Transfer Admittance	Y <sub>fs</sub>	-	12	-	S	$V_{DS} = -5V, I_D = -4A$	
Diode Forward Voltage	V <sub>SD</sub>	-	-0.8	-1.0	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss	-	1,326	-			
Output Capacitance	Coss	-	103	-	pF	$V_{DS} = -15V, V_{GS} = 0V, f = 1.0MHz$	
Reverse Transfer Capacitance	C <sub>rss</sub>	-	71	-			
Gate Resistance	Rg	-	7.3	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Qg	-	11.6	-			
Total Gate Charge (V <sub>GS</sub> = -10V)	Qg	-	25.1	-	nC		
Gate-Source Charge	Q <sub>gs</sub>	-	2	-		$V_{DD} = -15V, I_D = -4A$	
Gate-Drain Charge	Q <sub>gd</sub>	-	1.7	-			
Turn-On Delay Time	t <sub>D(on)</sub>	-	8	-			
Turn-On Rise Time	tr	-	13	-	-0	V <sub>DS</sub> = -15V, V <sub>GS</sub> = -10V,	
Turn-Off Delay Time	t <sub>D(off)</sub>	-	71	-	nS	$R_{GEN} = 6\Omega, R_L = 3.75\Omega$	
Turn-Off Fall Time	t <sub>f</sub>	-	38	-	1		

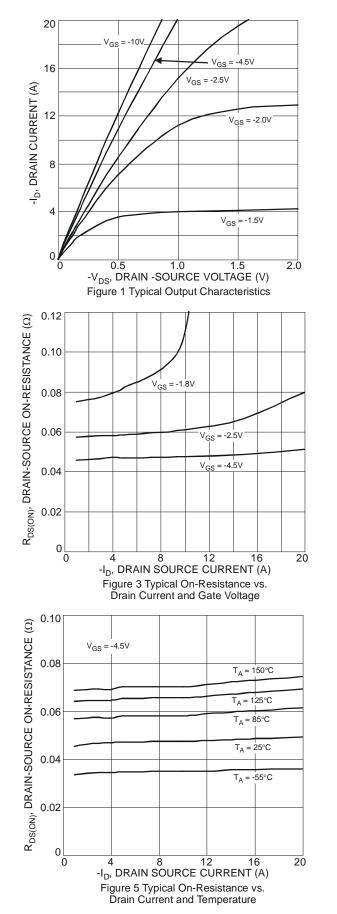
Notes: 6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

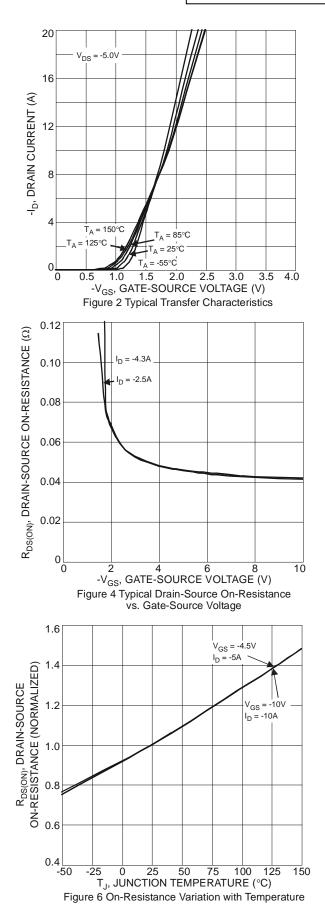
7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper pad layout

8 .Short duration pulse test used to minimize self-heating effect.

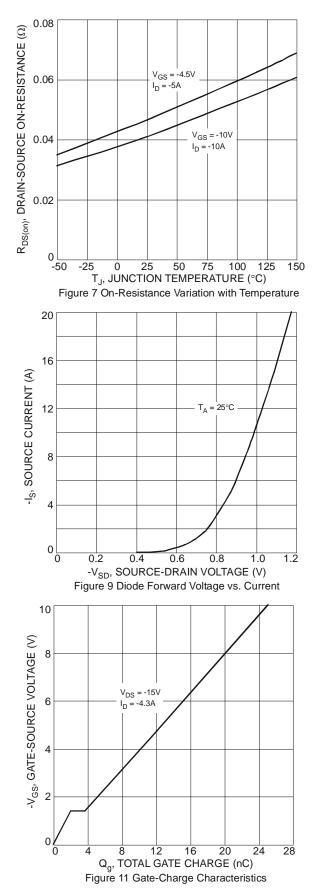
9. Guaranteed by design. Not subject to production testing.

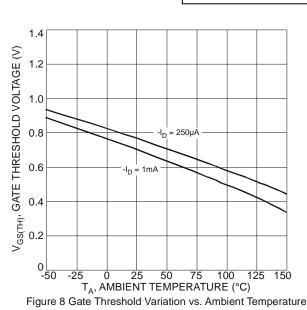


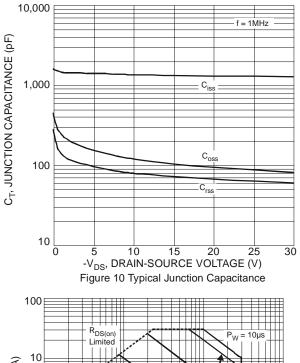


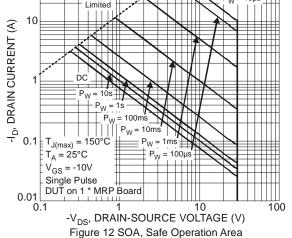




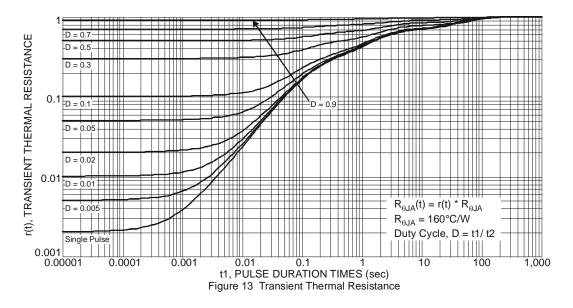






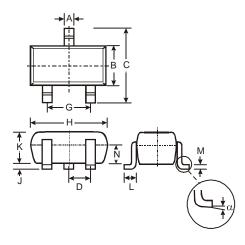






# **Package Outline Dimensions**

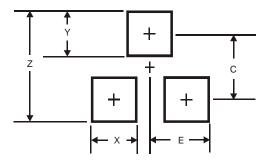
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SC59						
Dim	Min	Max	Тур			
Α	0.35	0.50	0.38			
В	1.50	1.70	1.60			
С	2.70	3.00	2.80			
D	-	-	0.95			
G	-	-	1.90			
Н	2.90	3.10	3.00			
J	0.013	0.10	0.05			
к	1.00	1.30	1.10			
L	0.35	0.55	0.40			
М	0.10	0.20	0.15			
Ν	0.70	0.80	0.75			
α	0°	8°	-			
All	Dimens	ions in	mm			

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	3.4
Х	0.8
Y	1.0
С	2.4
E	1.35



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